

CMOD3003

**SURFACE MOUNT
LOW LEAKAGE
SILICON SWITCHING DIODE**



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMOD3003 type is a silicon switching diode manufactured by the epitaxial planar process, epoxy molded in a ULTRAmimi™ surface mount package, designed for switching applications requiring an extremely low leakage diode.

MARKING CODE: 3C

ULTRAmimi™



SOD-523 CASE

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Continuous Reverse Voltage
Average Rectified Current
Continuous Forward Current
Peak Repetitive Forward Current
Peak Forward Surge Current, $t_p=1.0\mu\text{s}$
Peak Forward Surge Current, $t_p=1.0\text{s}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_R 180
 I_O 200
 I_F 600
 I_{FRM} 700
 I_{FSM} 2.0
 I_{FSM} 1.0
 P_D 250
 T_J, T_{stg} -65 to +150
 θ_{JA} 500

UNITS

V
mA
mA
mA
A
A
mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

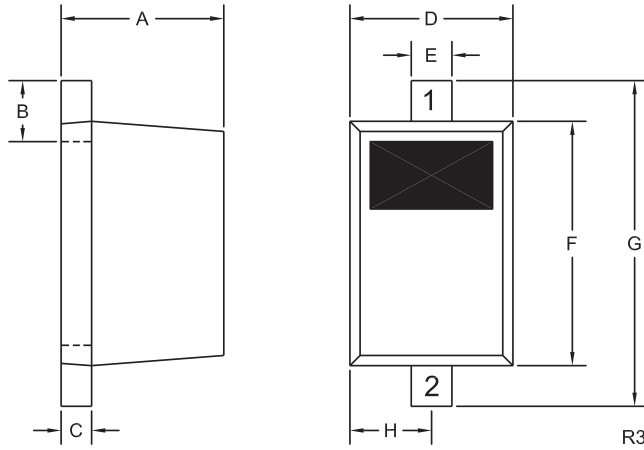
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=125\text{V}$		1.0	nA
I_R	$V_R=125\text{V}, T_A=150^\circ\text{C}$		3.0	μA
I_R	$V_R=180\text{V}$		10	nA
I_R	$V_R=180\text{V}, T_A=150^\circ\text{C}$		5.0	μA
BV_R	$I_R=5.0\mu\text{A}$	200		V
V_F	$I_F=1.0\text{mA}$	0.62	0.72	V
V_F	$I_F=10\text{mA}$	0.72	0.83	V
V_F	$I_F=50\text{mA}$	0.80	0.89	V
V_F	$I_F=100\text{mA}$	0.83	0.93	V
V_F	$I_F=200\text{mA}$	0.87	1.10	V
V_F	$I_F=300\text{mA}$	0.90	1.15	V
C_T	$V_R=0, f=1.0\text{MHz}$		4.0	pF

R3 (11-April 2011)

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SOD-523 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Cathode
- 2) Anode

MARKING CODE: 3C

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.020	0.031	0.50	0.80
B	0.008	0.016	0.20	0.40
C	0.002	0.008	0.05	0.20
D	0.028	0.035	0.70	0.90
E	0.008	0.014	0.20	0.35
F	0.039	0.055	1.00	1.40
G	0.055	0.071	1.40	1.80
H	0.016		0.40	

SOD-523 (REV: R3)

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